DATA SHEET

BF1101; BF1101R; BF1101WR
N-channel dual-gate MOS-FETs

Product specification
Supersedes data of 1999 Feb 01

1999 May 14

Philips
Semiconductors

PHILIPS

N-channel dual-gate MOS-FETs BF1101; BF1101R; BF1101WR

FEATURES

- Short channel transistor with high forward transfer admittance to input capacitance ratio
- Low noise gain controlled amplifier up to 1 GHz
- Partly internal self-biasing circuit to ensure good cross-modulation performance during AGC and good DC stabilization.

APPLICATIONS

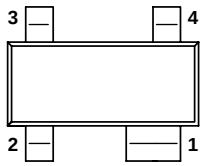
- VHF and UHF applications with 3 to 7 V supply voltage, such as television tuners and professional communications equipment.

DESCRIPTION

Enhancement type N-channel field-effect transistor with source and substrate interconnected. Integrated diodes between gates and source protect against excessive input voltage surges. The BF1101, BF1101R and BF1101WR are encapsulated in the SOT143B, SOT143R and SOT343R plastic packages respectively.

PINNING

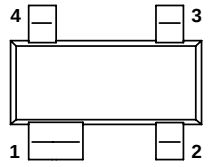
PIN	DESCRIPTION
1	source
2	drain
3	gate 2
4	gate 1



Top view MSB035

BF1101R marking code: NCp.

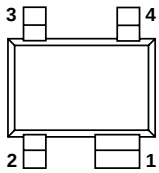
Fig.2 Simplified outline (SOT143R).



Top view MSB014

BF1101 marking code: NDp.

Fig.1 Simplified outline (SOT143B).



Top view MSB842

BF1101WR marking code: NC.

Fig.3 Simplified outline (SOT343R).

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{DS}	drain-source voltage		–	–	7	V
I_D	drain current		–	–	30	mA
P_{tot}	total power dissipation		–	–	200	mW
$\lvert y_{fs} \rvert$	forward transfer admittance		25	30	–	mS
$C_{ig1\text{-}ss}$	input capacitance at gate 1		–	2.2	2.7	pF
C_{rss}	reverse transfer capacitance	f = 1 MHz	–	25	35	fF
F	noise figure	f = 800 MHz	–	1.7	2.5	dB
X_{mod}	cross-modulation	input level for k = 1% at 40 dB AGC	100	–	–	dBμV
T_j	operating junction temperature		–	–	150	°C

CAUTION

This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A and SNW-FQ-302B.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage		–	7	V
I_D	drain current		–	30	mA
I_{G1}	gate 1 current		–	±10	mA
I_{G2}	gate 2 current		–	±10	mA
P_{tot}	total power dissipation	$T_s \leq 110$ °C; note 1	–	200	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	operating junction temperature		–	+150	°C

Note

1. T_s is the temperature of the soldering point of the source lead.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering point	200	K/W

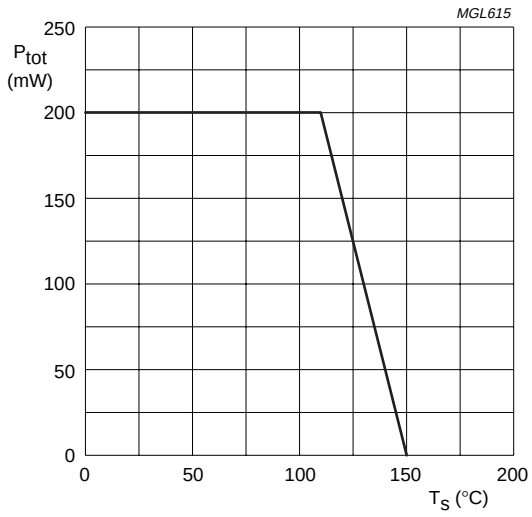


Fig.4 Power derating curve.

STATIC CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{G1-S} = V_{G2-S} = 0$; I_D = 10 µA	7	–	V
$V_{(BR)G1-SS}$	gate 1-source breakdown voltage	$V_{G2-S} = V_{DS} = 0$; I_{G1-S} = 10 mA	7	16	V
$V_{(BR)G2-SS}$	gate 2-source breakdown voltage	$V_{G1-S} = V_{DS} = 0$; I_{G2-S} = 10 mA	7	16	V
$V_{(F)S-G1}$	forward source-gate 1 voltage	$V_{G2-S} = V_{DS} = 0$; I_{S-G1} = 10 mA	0.5	1.5	V
$V_{(F)S-G2}$	forward source-gate 2 voltage	$V_{G1-S} = V_{DS} = 0$; I_{S-G2} = 10 mA	0.5	1.5	V
$V_{G1-S\ (th)}$	gate 1-source threshold voltage	V_{G2-S} = 4 V; V_{DS} = 5 V; I_D = 100 µA	0.3	1.0	V
$V_{G2-S\ (th)}$	gate 2-source threshold voltage	V_{G1-S} = 5 V; V_{DS} = 5 V; I_D = 100 µA	0.3	1.2	V
I_{DSX}	drain-source current	V_{G2-S} = 4 V; V_{DS} = 5 V; R_{G1} = 120 kΩ; note 1	8	16	mA
I_{G1-SS}	gate 1 cut-off current	$V_{G2-S} = V_{DS} = 0$; V_{G1-S} = 5 V	–	50	nA
I_{G2-SS}	gate 2 cut-off current	$V_{G1-S} = V_{DS} = 0$; V_{G2-S} = 4 V	–	20	nA

Note

1. R_{G1} connects G_1 to V_{GG} = 5 V; see Fig.21.

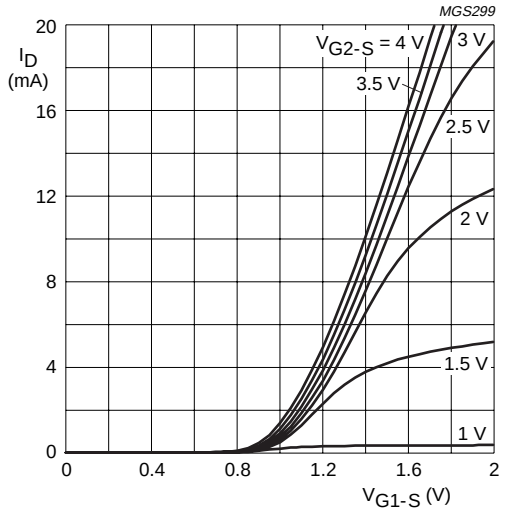
DYNAMIC CHARACTERISTICS

Common source; T_{amb} = 25 °C; V_{G2-S} = 4 V; V_{DS} = 5 V; I_D = 12 mA; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$\lvert y_{fs} \rvert$	forward transfer admittance	pulsed; T_j = 25 °C	25	30	40	mS
C_{ig1-ss}	input capacitance at gate 1	f = 1 MHz	–	2.2	2.7	pF
C_{ig2-ss}	input capacitance at gate 2	f = 1 MHz	–	1.6	–	pF
C_{oss}	output capacitance	f = 1 MHz	–	1.2	–	pF
C_{rss}	reverse transfer capacitance	f = 1 MHz	–	25	35	fF
F	noise figure	f = 800 MHz; $Y_S = Y_{S\ opt}$	–	1.7	2.5	dB
X_{mod}	cross-modulation	input level for k = 1% at 0 dB AGC; f_w = 50 MHz; f_{unw} = 60 MHz; note 1	85	–	–	dBµV
		input level for k = 1% at 40 dB AGC; f_w = 50 MHz; f_{unw} = 60 MHz; note 1	100	–	–	dBµV

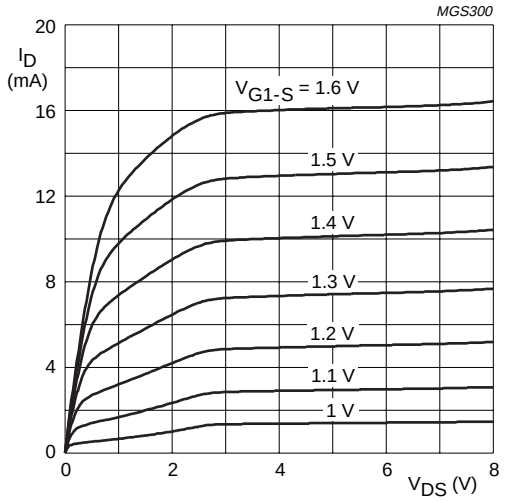
Note

1. Measured in test circuit of Fig.21.



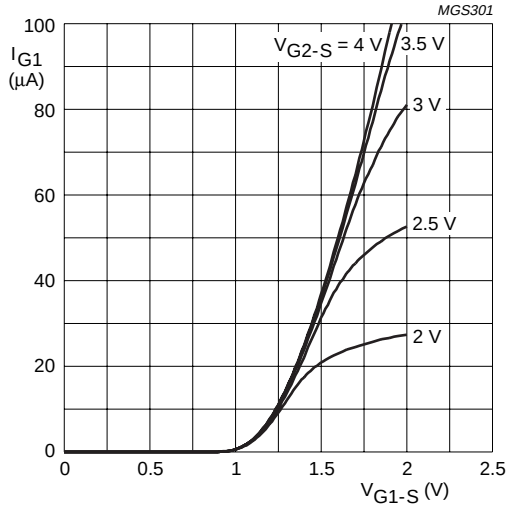
V_{DS} = 5 V.
T_j = 25 °C.

Fig.5 Transfer characteristics; typical values.



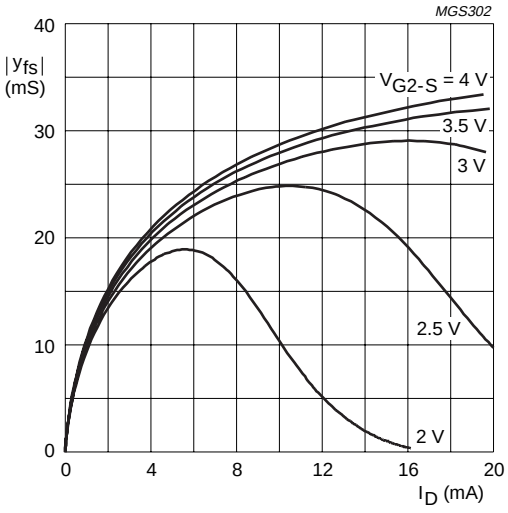
V_{G2-S} = 4 V.
T_j = 25 °C.

Fig.6 Output characteristics; typical values.



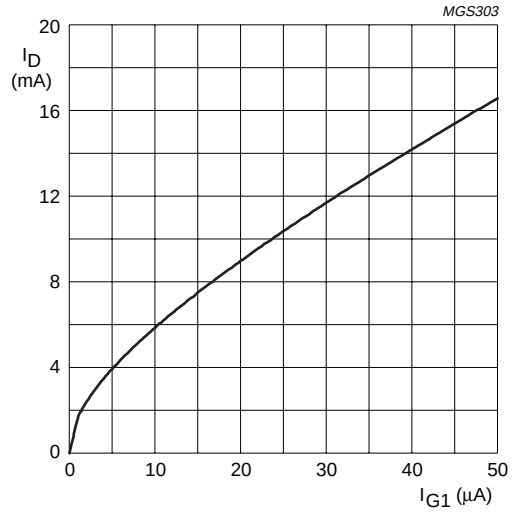
V_{DS} = 5 V.
T_j = 25 °C.

Fig.7 Gate 1 current as a function of gate 1 voltage; typical values.



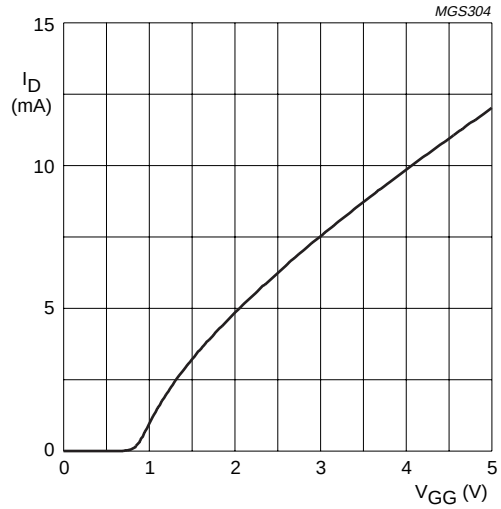
V_{DS} = 5 V.
T_j = 25 °C.

Fig.8 Forward transfer admittance as a function of drain current; typical values.



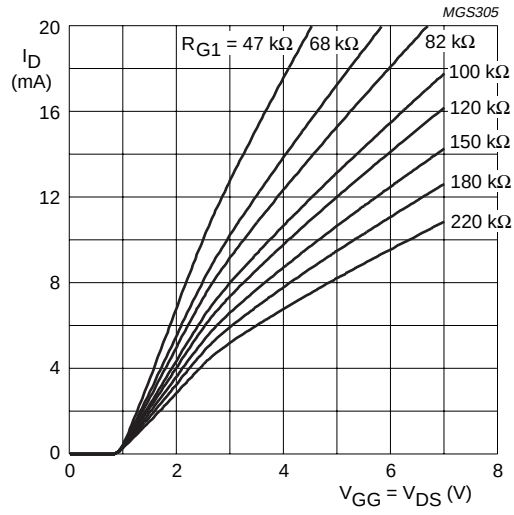
V_{DS} = 5 V.
V_{G2-S} = 4 V.
T_j = 25 °C.

Fig.9 Drain current as a function of gate 1 current; typical values.



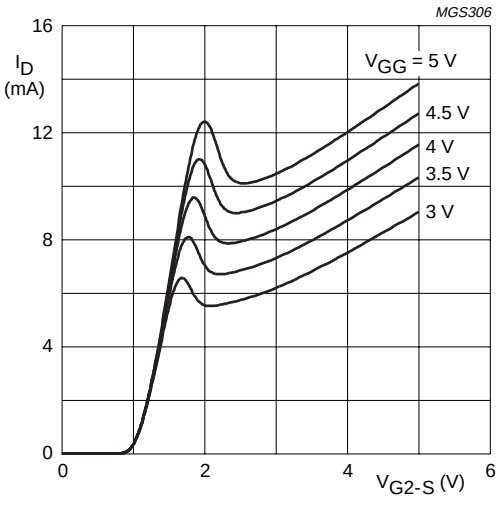
V_{DS} = 5 V; V_{G2-S} = 4 V; T_j = 25 °C.
R_{G1} = 120 kΩ (connected to V_{GG}); see Fig.21.

Fig.10 Drain current as a function of gate 1 supply voltage (= V_{GG}); typical values.



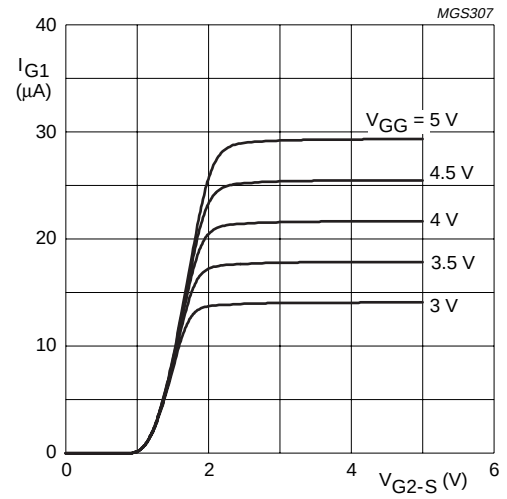
V_{G2-S} = 4 V; T_j = 25 °C.
R_{G1} connected to V_{GG}; see Fig.21.

Fig.11 Drain current as a function of gate 1 (= V_{GG}) and drain supply voltage; typical values.



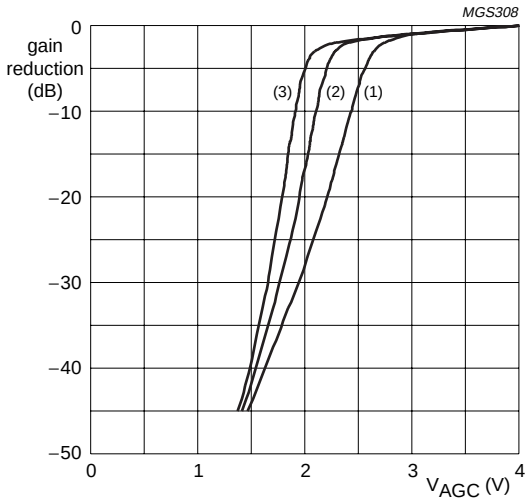
V_{DS} = 5 V; T_j = 25 °C.
R_{G1} = 120 kΩ (connected to V_{GG}); see Fig.21.

Fig.12 Drain current as a function of gate 2 voltage; typical values.



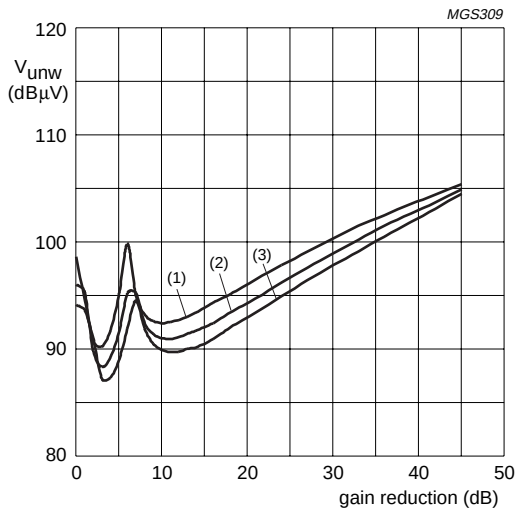
V_{DS} = 5 V; T_j = 25 °C.
R_{G1} = 120 kΩ (connected to V_{GG}); see Fig.21.

Fig.13 Gate 1 current as a function of gate 2 voltage; typical values.



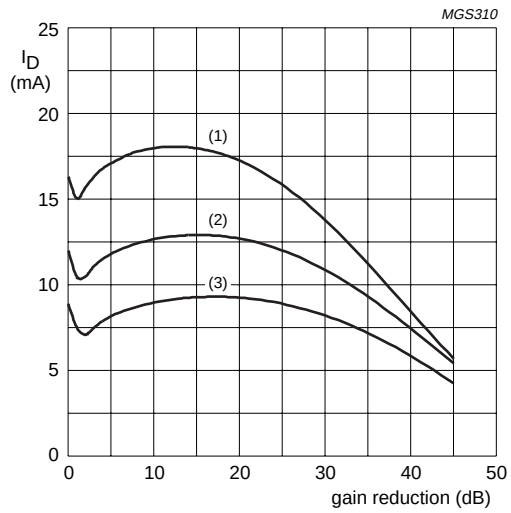
V_{DS} = 5 V; V_{GG} = 5 V; f = 50 MHz; T_{amb} = 25 °C.
(1) R_{G1} = 68 kΩ. (2) R_{G1} = 120 kΩ. (3) R_{G1} = 180 kΩ.

Fig.14 Typical gain reduction as a function of the AGC voltage; see Fig.21.



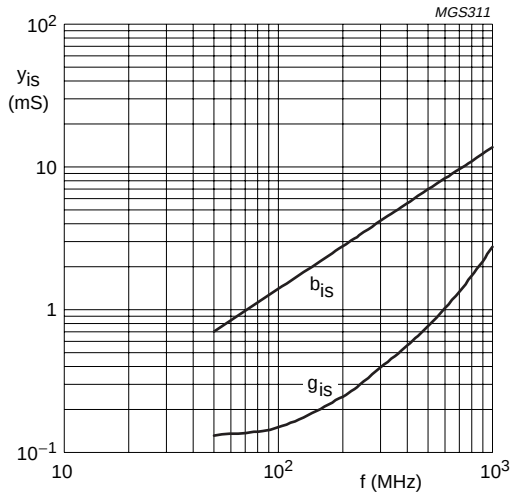
V_{DS} = 5 V; V_{GG} = 5 V; f = 50 MHz; f_{unw} = 60 MHz; T_{amb} = 25 °C.
(1) R_{G1} = 68 kΩ. (2) R_{G1} = 120 kΩ. (3) R_{G1} = 180 kΩ.

Fig.15 Unwanted voltage for 1% cross-modulation as a function of gain reduction; typical values; see Fig.21.



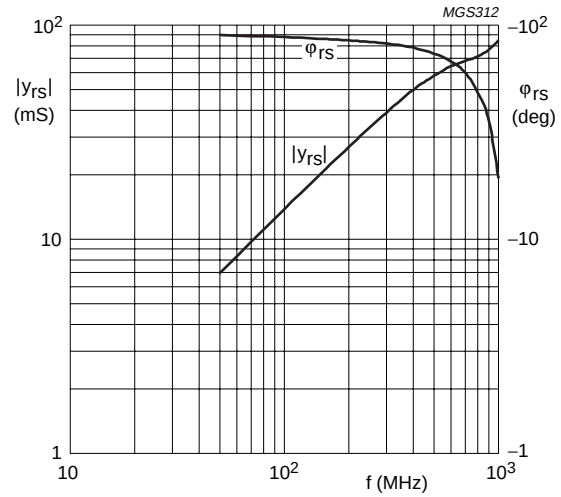
V_{DS} = 5 V; V_{GG} = 5 V; f = 50 MHz; T_{amb} = 25 °C.
(1) R_{G1} = 68 kΩ. (2) R_{G1} = 120 kΩ. (3) R_{G1} = 180 kΩ.

Fig.16 Drain current as a function of gain reduction; typical values; see Fig.21.



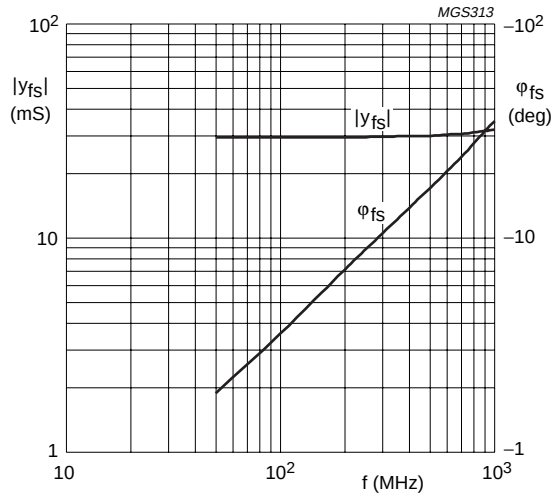
V_{DS} = 5 V; V_{G2} = 4 V.
I_D = 12 mA; T_{amb} = 25 °C.

Fig.17 Input admittance as a function of frequency; typical values.



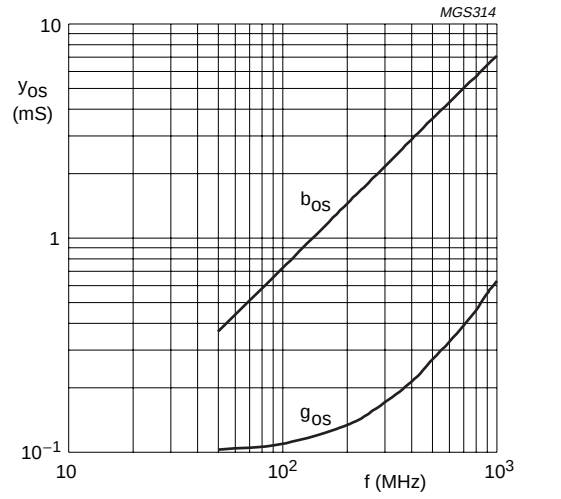
V_{DS} = 5 V; V_{G2} = 4 V.
I_D = 12 mA; T_{amb} = 25 °C.

Fig.18 Reverse transfer admittance and phase as a function of frequency; typical values.



V_{DS} = 5 V; V_{G2} = 4 V.
I_D = 12 mA; T_{amb} = 25 °C.

Fig.19 Forward transfer admittance and phase as a function of frequency; typical values.



V_{DS} = 5 V; V_{G2} = 4 V.
I_D = 12 mA; T_{amb} = 25 °C.

Fig.20 Output admittance as a function of frequency; typical values.

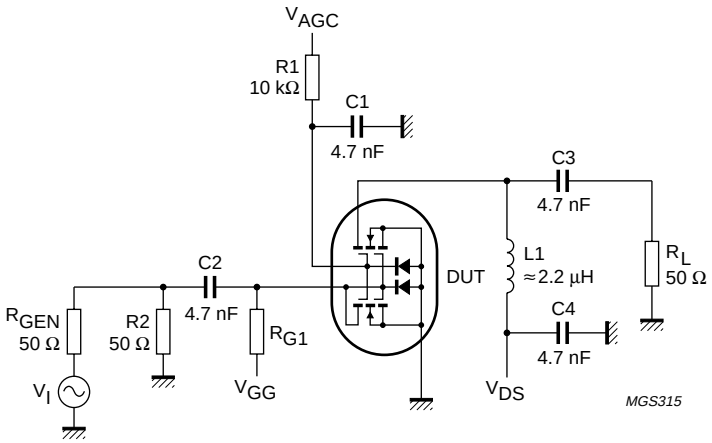


Fig.21 Cross-modulation test set-up.

Table 1 Scattering parameters: V_{DS} = 5 V; $V_{G2\text{-}S}$ = 4 V; I_D = 12 mA; T_{amb} = 25 °C

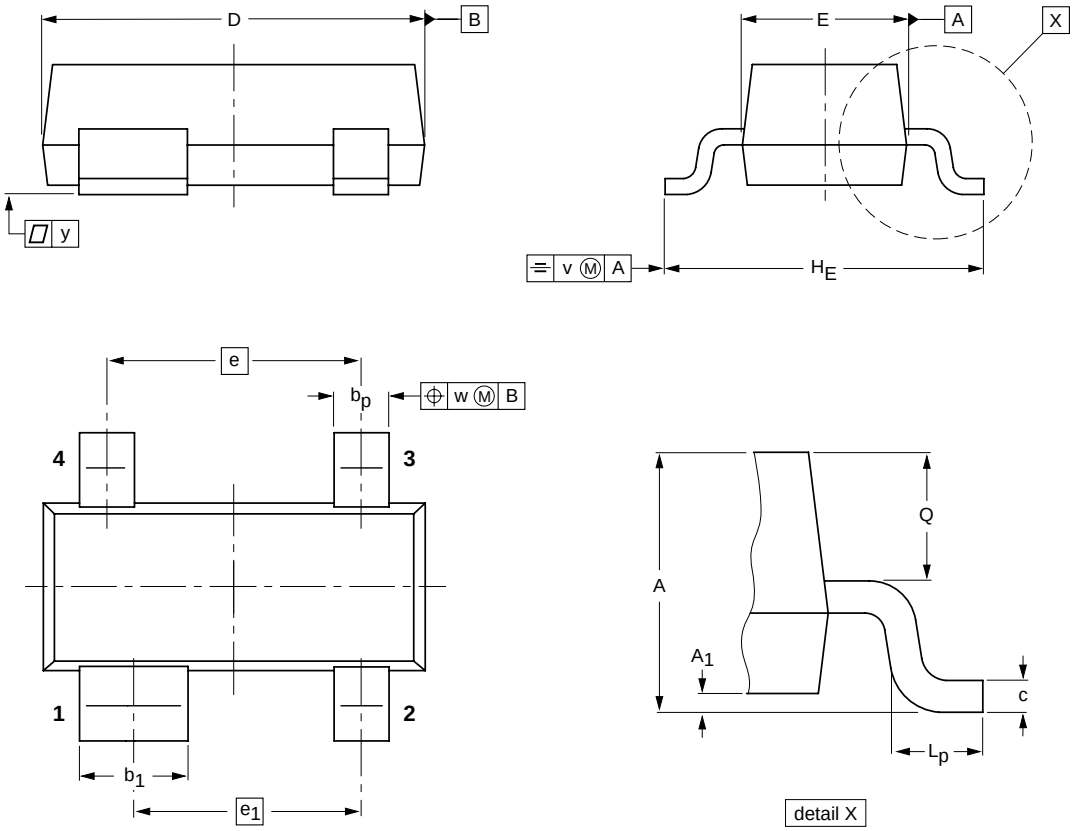
f (MHz)	S_{11}		S_{21}		S_{12}		S_{22}	
	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)
50	0.987	–4.1	2.922	175.0	0.001	87.6	0.990	–2.2
100	0.985	–8.1	2.908	170.3	0.001	86.1	0.989	–4.3
200	0.976	–16.1	2.875	160.8	0.003	83.3	0.985	–8.5
300	0.963	–23.9	2.820	157.6	0.004	80.4	0.982	–12.6
400	0.949	–31.6	2.762	142.6	0.005	78.2	0.977	–16.8
500	0.933	–38.8	2.665	134.1	0.005	77.8	0.972	–20.8
600	0.916	–45.7	2.591	125.7	0.005	78.9	0.967	–24.7
700	0.897	–52.2	2.498	117.7	0.006	81.8	0.961	–28.5
800	0.877	–58.4	2.410	109.6	0.005	89.1	0.957	–32.2
900	0.856	–64.5	2.318	101.6	0.006	97.1	0.950	–35.8
1000	0.832	–70.3	2.214	94.2	0.006	110.4	0.946	–39.6

Table 2 Noise data: V_{DS} = 5 V; $V_{G2\text{-}S}$ = 4 V; I_D = 12 mA; T_{amb} = 25 °C

f (MHz)	F_{min} (dB)	Γ_{opt}		R_n (Ω)
		(ratio)	(deg)	
800	1.5	0.715	58.3	37.85

PACKAGE OUTLINES

Plastic surface mounted package; 4 leads **SOT143B**

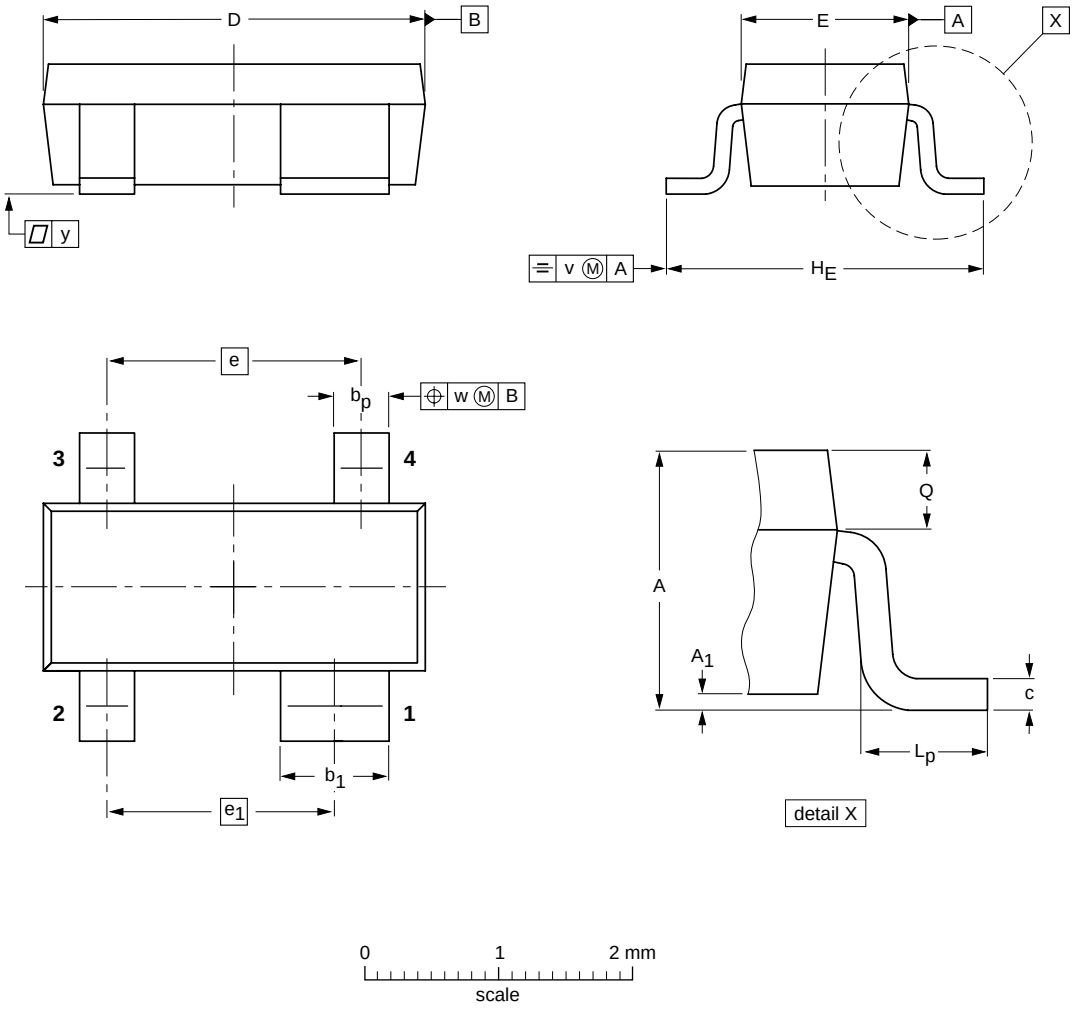


DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	b_1	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.9	0.1	0.48 0.38	0.88 0.78	0.15 0.09	3.0 2.8	1.4 1.2	1.9	1.7	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT143B						97-02-28

Plastic surface mounted package; reverse pinning; 4 leads **SOT143R**

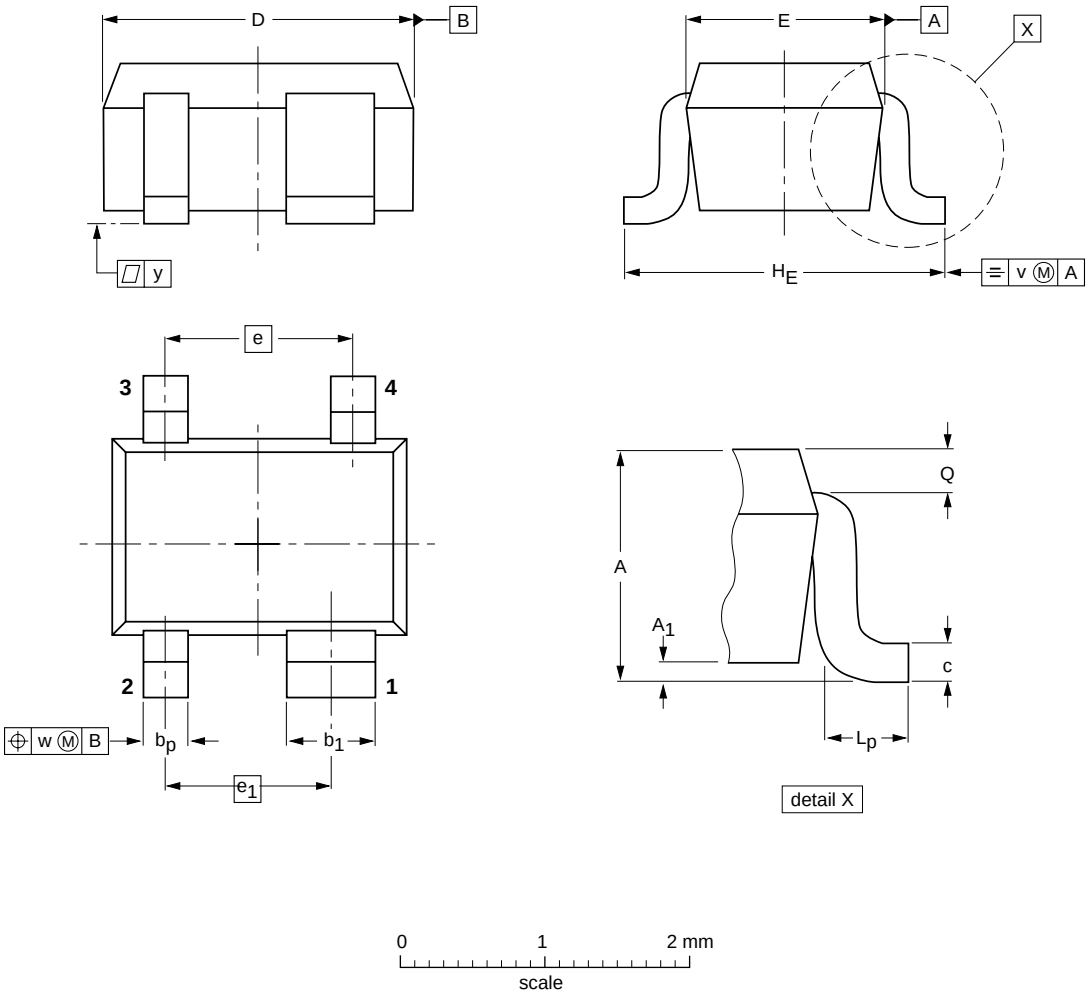


DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	b_1	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.9	0.1	0.48 0.38	0.88 0.78	0.15 0.09	3.0 2.8	1.4 1.2	1.9	1.7	2.5 2.1	0.55 0.25	0.45 0.25	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT143R						97-03-10

Plastic surface mounted package; reverse pinning; 4 leads **SOT343R**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	b_1	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.8	0.1	0.4 0.3	0.7 0.5	0.25 0.10	2.2 1.8	1.35 1.15	1.3	1.15	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT343R						97-05-21

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

NOTES

NOTES

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